





500V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR IN SOT23

Features

- BV_{CEO} > -500V
- I_C = -150mA high Continuous Collector Current
- Excellent h_{FE} Characteristics up to I_C = 100mA
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

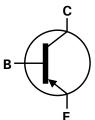
Mechanical Data

- Case: SOT23
- · Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight 0.008 grams (approximate)

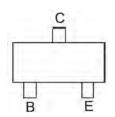
SOT23







Device Symbol



Top View Pin-Out

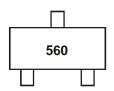
Ordering Information (Notes 4 & 5)

| Product | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|------------|------------|---------|--------------------|-----------------|-------------------|
| FMMT560TA | AEC-Q101 | 560 | 7 | 8 | 3,000 |
| FMMT560TC | AEC-Q101 | 560 | 13 | 8 | 10,000 |
| FMMT560QTA | Automotive | 560 | 7 | 8 | 3,000 |
| FMMT560QTC | Automotive | 560 | 13 | 8 | 10,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information



560 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|-----------------|-------|------|
| Collector-Base Voltage | V_{CBO} | -500 | V |
| Collector-Emitter Voltage | V_{CEO} | -500 | V |
| Emitter-Base Voltage | V_{EBO} | -7 | V |
| Continuous Collector Current | Ic | -150 | mA |
| Peak Pulse Current | I _{CM} | -500 | mA |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|-----------------------------------|-----------------|------|------|
| Power Dissipation | (Note 6) | P _D | 500 | mW |
| Thermal Resistance, Junction to Ambient (Note 6) | | $R_{	heta JA}$ | 250 | °C/W |
| Thermal Resistance, Junction to Lead (Note 7) | | $R_{\theta JL}$ | 194 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C | |

ESD Ratings (Note 8)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|---------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | ≥ 8,000 | V | 3B |
| Electrostatic Discharge - Machine Model | ESD MM | ≥ 400 | V | С |

Notes:

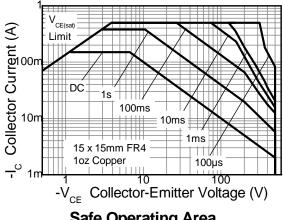
^{6.} For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

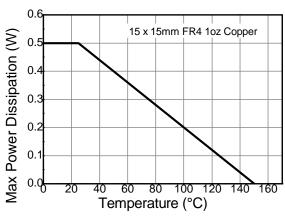
^{7.} Thermal resistance from junction to solder-point (at the end of the collector lead).

^{8.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



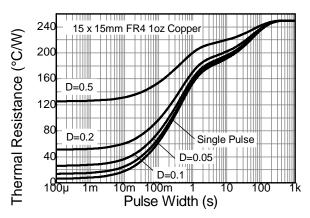
Thermal Characteristics and Derating Information

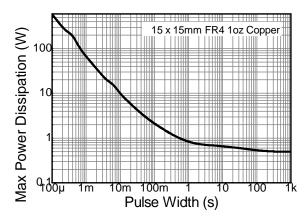




Safe Operating Area

Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation





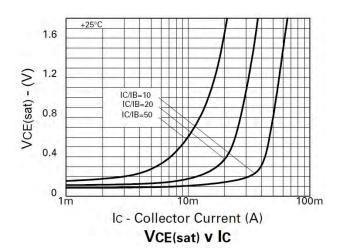
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

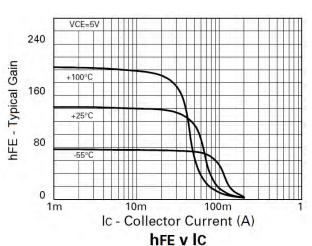
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|----------------------|----------------|--------------|-----------------|------|---|
| Collector-Base Breakdown Voltage | BV _{CBO} | -500 | - | - | V | $I_{C} = -100 \mu A$ |
| Collector-Emitter Breakdown Voltage (Note 9) | BV_CEO | -500 | - | - | V | $I_C = -1mA$ |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -7 | - | - | V | $I_E = -100 \mu A$ |
| Collector Cutoff Current | I _{CBO} | - | - | -100 | nA | V _{CB} = -500V |
| Emitter Cutoff Current | I _{EBO} | - | - | -100 | nA | $V_{EB} = -5V$ |
| Static Forward Current Transfer Ratio (Note 9) | h _{FE} | 100 80 - | - - 15 | 300 300 - | - | $I_C = -1mA$, $V_{CE} = -10V$ $I_C = -50mA$, $V_{CE} = -10V$ $I_C = -100mA$, $V_{CE} = -10V$ |
| Collector-Emitter Saturation Voltage (Note 9) | V _{CE(sat)} | - | - | -200 -500 | mV | $I_C = -20mA$, $I_B = -2mA$ $I_C = -50mA$, $I_B = -10mA$ |
| Base-Emitter Saturation Voltage (Note 9) | V _{BE(sat)} | - | - | -0.9 | V | $I_C = -50 \text{mA}, I_B = -10 \text{mA}$ |
| Base-Emitter Turn-On Voltage (Note 9) | V _{BE(on)} | - | - | -0.9 | V | $I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$ |
| Output Capacitance | C _{obo} | - | - | 8 | pF | V _{CB} = -20V, f = 1MHz |
| Transition Frequency | fτ | 60 | - | - | MHz | $V_{CE} = -20V$, $I_{C} = -10mA$, $f = 50MHz$ |
| Turn-On Time | t _{on} | - | 110 | - | ns | V _{CE} = -100V, I _C = -50mA, |
| Turn-Off Time | t _{off} | - | 1.5 | - | μs | $I_{B1} = -5mA$, $I_{B2} = 10mA$ |

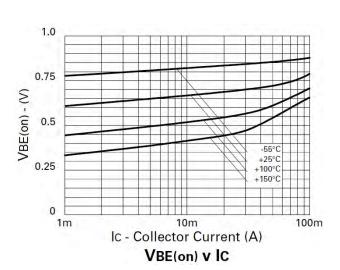
Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

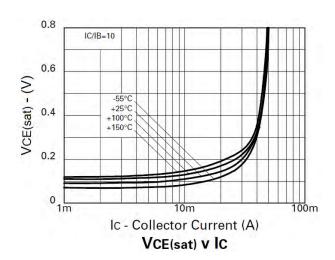


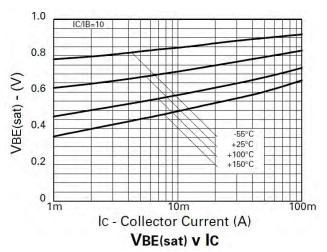
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







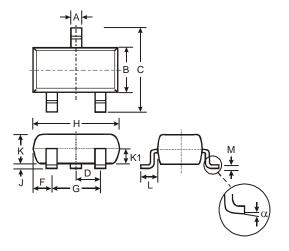






Package Outline Dimensions

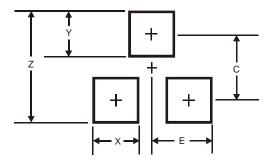
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT23 | | | | | |
|----------------------|-------|------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 0.37 | 0.51 | 0.40 | | |
| В | 1.20 | 1.40 | 1.30 | | |
| С | 2.30 | 2.50 | 2.40 | | |
| D | 0.89 | 1.03 | 0.915 | | |
| F | 0.45 | 0.60 | 0.535 | | |
| G | 1.78 | 2.05 | 1.83 | | |
| Η | 2.80 | 3.00 | 2.90 | | |
| 7 | 0.013 | 0.10 | 0.05 | | |
| K | 0.903 | 1.10 | 1.00 | | |
| K 1 | - | - | 0.400 | | |
| L | 0.45 | 0.61 | 0.55 | | |
| М | 0.085 | 0.18 | 0.11 | | |
| α | 0° | 8° | - | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| Х | 8.0 |
| Υ | 0.9 |
| С | 2.0 |
| E | 1.35 |





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Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru_4 moschip.ru_9